

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listings of Claims:

- 1. (canceled)
- 2. (currently amended) <u>A The</u> semiconductor die package of Claim-1 comprising:

a semiconductor die;

a capsule enclosing said die;

a plurality of metal studs, each of said metal studs protruding from a bottom surface of said capsule, each of said metal studs having a flat bottom surface; and

a plurality of bonding wires, each of said bonding wires extending between a first bonding location on said die and a second bonding location adjacent an upper surface of one of said metal studs, said bonding wires and bonding locations being embedded within said capsule;

wherein said studs comprise a first metal, a layer of a second metal being formed on said flat bottom surfaces of said studs.

- 3. (original) The semiconductor die package of Claim 2 wherein said first metal is a copper alloy and said second metal comprises nickel.
- 4. (currently amended) <u>A</u> The semiconductor die package of Claim 3 comprising:

a semiconductor die;

a capsule enclosing said die;

a plurality of metal studs, each of said metal studs protruding from a bottom surface of said capsule, each of said metal studs having a flat bottom surface; and

a plurality of bonding wires, each of said bonding wires extending between a first bonding location on said die and a second bonding location adjacent an upper surface of one of said metal studs, said bonding wires and bonding locations being embedded within said capsule;

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wherein said studs comprise a first metal, a layer of a second metal being formed on said flat bottom surfaces of said studs, wherein said first metal is a copper alloy and wherein said second metal comprises Ni/Pd/Au.

5. (currently amended) <u>A The</u> semiconductor die package of Claim 1 comprising:

a semiconductor die;

a capsule enclosing said die;

a plurality of metal studs, each of said metal studs protruding from a bottom surface of said capsule, each of said metal studs having a flat bottom surface; and

a plurality of bonding wires, each of said bonding wires extending between a first bonding location on said die and a second bonding location adjacent an upper surface of one of said metal studs, said bonding wires and bonding locations being embedded within said capsule;

wherein lateral surfaces of the portions of said studs that protrude from said bottom surface of said capsule are beveled.

- 6. (currently amended) The semiconductor die package of Claim <u>2</u> 4 comprising a second layer of said second metal formed on said upper surface of each of said studs.
- 7. (currently amended) The semiconductor die package of Claim <u>2</u> 4 wherein said studs are arranged in a single row on at least one side of said die.
- 8. (currently amended) The semiconductor die package of Claim <u>2</u> 4 wherein said studs are arranged in a plurality of rows on at least one side of said die.
- 9. (currently amended) <u>A The</u> semiconductor die package of Claim 1 comprising:

a semiconductor die;

a capsule enclosing said die;

a plurality of metal studs, each of said metal studs protruding from a bottom surface of said capsule, each of said metal studs having a flat bottom surface; and a plurality of bonding wires, each of said bonding wires extending between a first bonding location on said die and a second bonding location adjacent an upper

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surface of one of said metal studs, said bonding wires and bonding locations being embedded within said capsule;

wherein said die rests on a layer of epoxy, a bottom surface of said layer of epoxy being exposed at a bottom of said package.

10. (currently amended) <u>A</u> The semiconductor die package of Claim 1 comprising:

a semiconductor die;

a capsule enclosing said die;

a plurality of metal studs, each of said metal studs protruding from a bottom surface of said capsule, each of said metal studs having a flat bottom surface; and

a plurality of bonding wires, each of said bonding wires extending between a first bonding location on said die and a second bonding location adjacent an upper surface of one of said metal studs, said bonding wires and bonding locations being embedded within said capsule;

wherein said die rests on a layer of epoxy, said layer of epoxy being attached to a plated metal layer, a bottom surface of said plated metal layer being exposed at a bottom of said package.

- 11. (currently amended) The semiconductor die package of Claim <u>2</u> 4 comprising a die-attach pad, said semiconductor die being attached to said <u>die-attach</u> die attach pad.
- 12. (original) The semiconductor die package of Claim 11 wherein said die is attached to said die-attach pad by means of an epoxy layer and a plated metal layer.
- 13. (original) The semiconductor die package of Claim 11 comprising a metal layer plated on a bottom surface of said die-attach pad.
- 14. (original) The semiconductor die package of Claim 11 wherein said dieattach pad is of substantially the same thickness as the studs.
- 15. (original) The semiconductor die package of Claim 11 wherein said dieattach pad is thinner than said studs.

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- 16. (currently amended) The semiconductor die package of Claim 15 wherein a bottom top surface of said die-attach pad is substantially coplanar with said bottom surface of said capsule.
- 17. (currently amended) The semiconductor die package of Claim 15 wherein said die-attach pad is approximately one-half as thick as said studs.
- 18. (original) The semiconductor die package of Claim 11 wherein a lateral dimension of said die-attach pad is smaller than a lateral dimension of said die.
- 19. (currently amended) <u>A</u> The semiconductor die package of Claim 18 comprising:

a semiconductor die;

a die-attach pad, said semiconductor die being attached to said die-attach pad, a lateral dimension of said die-attach pad being smaller than a lateral dimension of said die;

a capsule enclosing said die;

a plurality of metal studs, each of said metal studs protruding from a bottom surface of said capsule, each of said metal studs having a flat bottom surface; and

a plurality of bonding wires, each of said bonding wires extending between a first bonding location on said die and a second bonding location adjacent an upper surface of one of said metal studs, said bonding wires and bonding locations being embedded within said capsule;

wherein said die is attached to said die-attach pad by means of an epoxy layer and a plated metal layer, said plated metal layer having a lateral dimension larger than said lateral dimension of said die.

- 20. (original) The semiconductor die package of Claim 19 wherein a portion of a lower surface of said plated metal layer is exposed.
- 21. (original) The semiconductor die package of Claim 11 wherein a cavity is formed in an upper surface of said die-attach pad, said die being positioned in said cavity.
- 22. (currently amended) <u>A</u> The semiconductor die package of Claim 11 comprising:

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a semiconductor die;

<u>a die-attach pad, said semiconductor die being attached to said die-attach</u> pad;

a capsule enclosing said die;

a plurality of metal studs, each of said metal studs protruding from a bottom surface of said capsule, each of said metal studs having a flat bottom surface; and

a plurality of bonding wires, each of said bonding wires extending between a first bonding location on said die and a second bonding location adjacent an upper surface of one of said metal studs, said bonding wires and bonding locations being embedded within said capsule;

wherein a moat is formed in an upper surface of said die-attach pad, said moat surrounding said die.

- 23. (currently amended) The semiconductor die package of Claim 11 comprising a plurality of semiconductor dice and a plurality of die-attach pads, each of said dice being mounted on one of said die-attach pads.24.
- 24. (original) The semiconductor die package of Claim 11 wherein said dieattach pad has a thicker portion and a thinner portion said thicker and thinner portions being connected by a graduated step on a bottom surface of said die-attach pad.
- 25. (original) The semiconductor die package of Claim 11 wherein said dieattach pad is slotted.
- 26. (currently amended) The semiconductor die package of Claim <u>2</u> 4 wherein said die is mounted on said studs.
 - 27. (original) A semiconductor die package comprising:
 - a semiconductor die;
 - a capsule enclosing said die; and
 - a plurality of metal studs, each of said metal studs protruding from a bottom surface of said capsule, each of said metal studs having a flat bottom surface, said die being mounted on said studs by means for solder balls, each of said solder balls making an electrical connection between a location on said die and one of said studs, said solder balls being embedded within said capsule.

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- (original) The semiconductor die package of Claim 27 wherein some or all of 28. said studs comprise a shelf portion, said solder balls being in contact with said shelf portions.
- (currently amended) The semiconductor die package of Claim 27 further 29. comprising a die-attach pad, said die being mounted on said die-attach die-attached pad by means of one or more solder balls.
 - (original) A process of fabricating a semiconductor die package comprising: 30. providing a metal sheet; forming a first mask layer on a first side of said metal sheet: partially etching said metal sheet through openings in said first mask layer; attaching a semiconductor die to a location on said first side of said metal sheet;

applying a layer of a molding compound over said first side of said metal sheet:

forming a second mask layer on a second side of said metal sheet; and partially etching said metal sheet through openings in said second mask layer to form a plurality of studs.

- (original) The method of Claim 30 wherein forming a first mask layer 31. comprises forming a photoresist layer and photolithographically patterning said photoresist layer.
- (original) The method of Claim 30 wherein forming a second mask layer 32. comprises plating a metal layer.
- 33. (new) The semiconductor die package of Claim 9 wherein a plane defined by said bottom surface of said layer of epoxy is located above a plane defined by said flat bottom surfaces of said metal studs.
- (new) The semiconductor die package of Claim 33 wherein said bottom 34. ission College Blve surface of said layer of epoxy is coplanar with a bottom surface of said capsule.

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- 35. (new) The semiconductor die package of Claim 10 wherein a plane defined by said bottom surface of said plated metal layer is located above a plane defined by said flat bottom surfaces of said metal studs.
- 36. (new) The semiconductor die package of Claim 35 wherein said bottom surface of said plated metal layer is coplanar with a bottom surface of said capsule.
- 37. (new) The semiconductor die package of Claim 10 wherein a lateral dimension of said plated metal layer is greater than a lateral dimension of said die.